

Electronic Supplementary Information

Manipulating the adhesion of electroless nickel-phosphorus film on silicon wafers by silane compound modification and rapid thermal annealing

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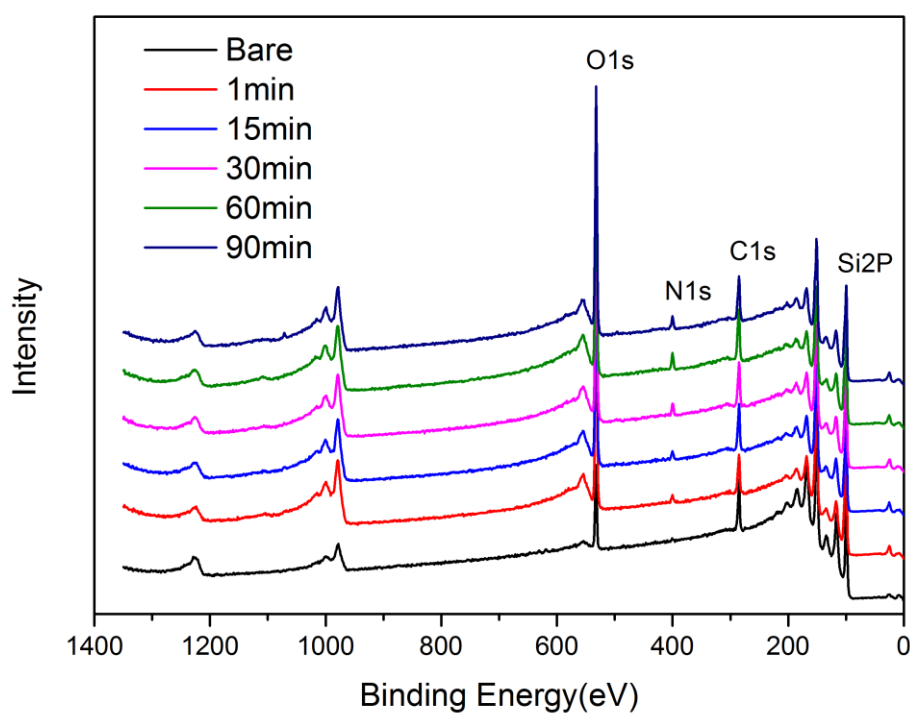


Figure S1. XPS wide spectrum of bare and various ETAS-modified Si wafers

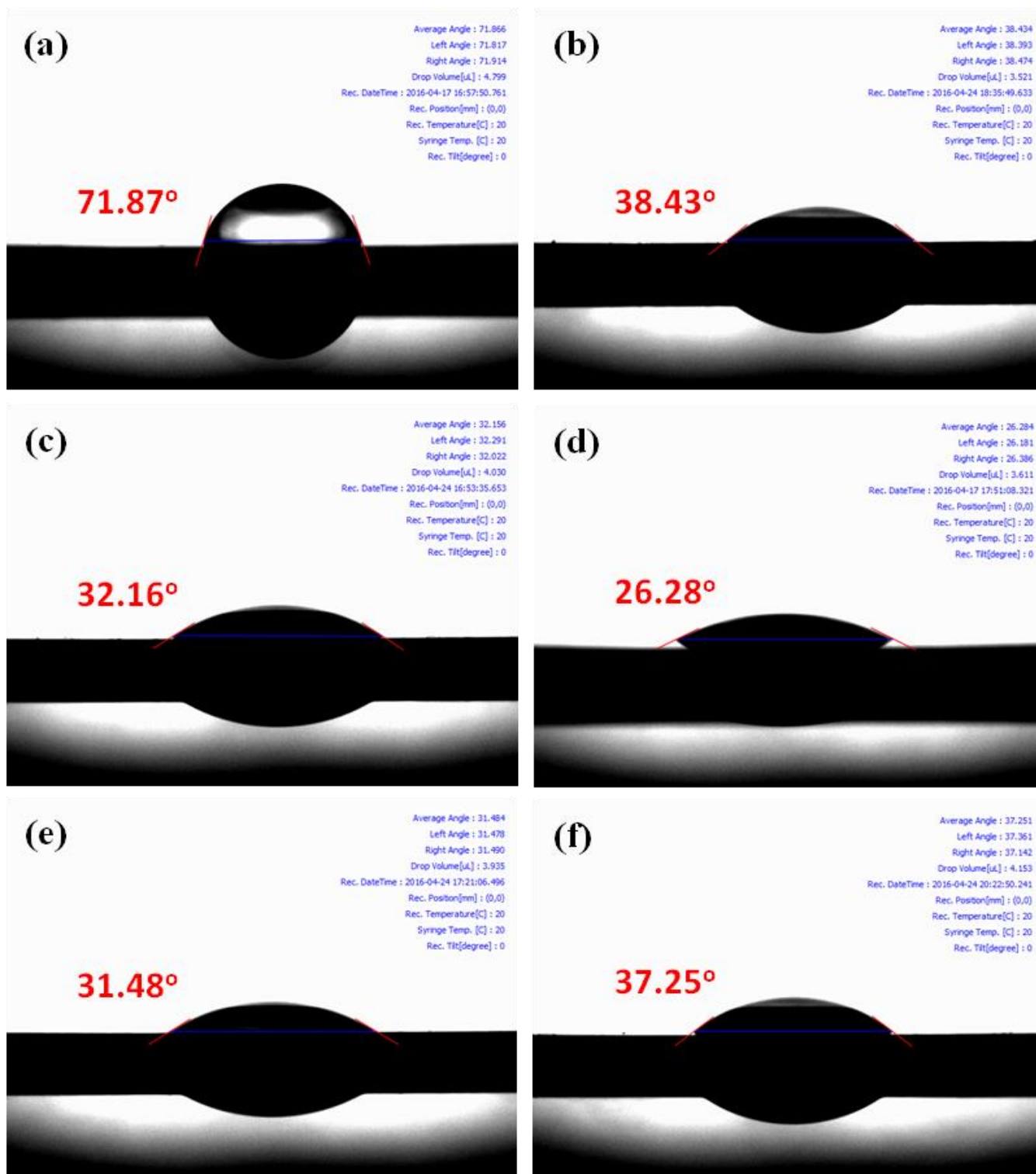


Figure S2. Representative WCA images of (a) bare wafer, (b) ETAS-1, (c) ETAS-15, (d) ETAS-30, (e) ETAS-60 and (f)

ETAS-90.

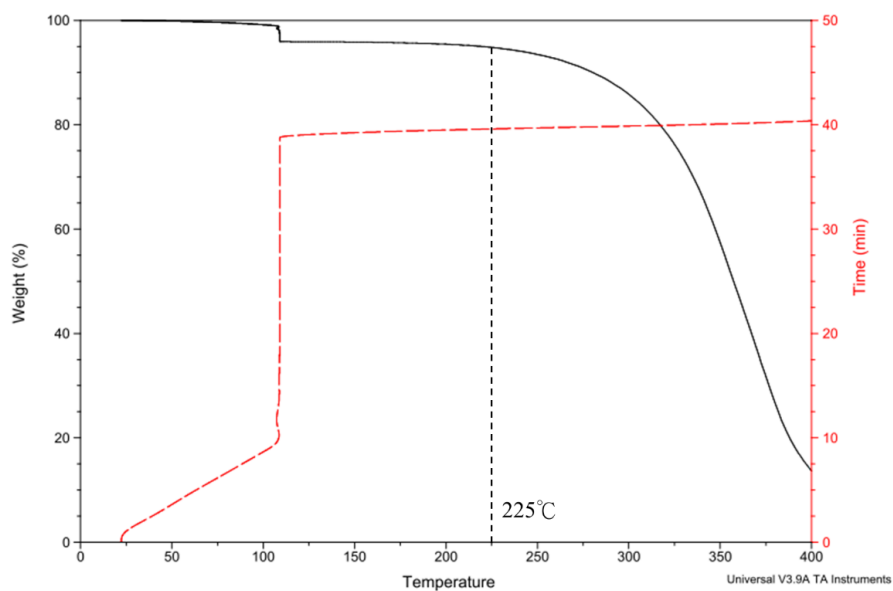


Figure S3. TGA curve of pure ETAS

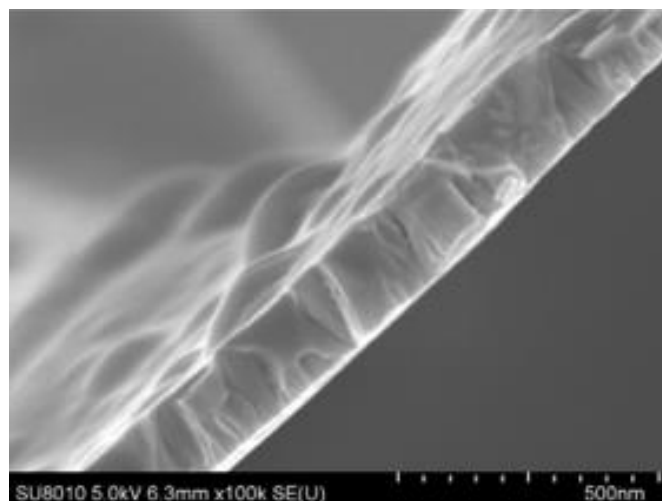


Figure S4. Typical ELP Ni-P film thickness (approximately 200nm) fabricated in this study.